

HL8335MG

GaAlAs Laser Diode

ODE-208-058B (Z)

Rev.2

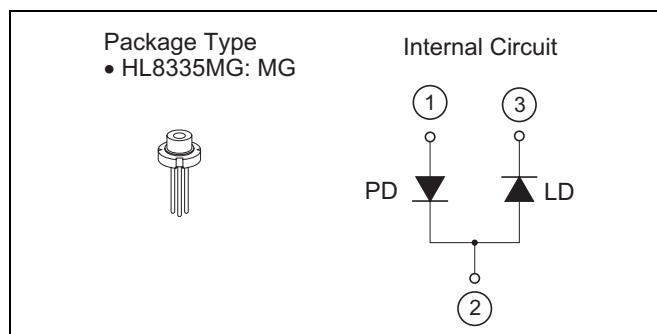
Jun. 13, 2006

Description

The HL8335MG is a high-power 0.8 μm band GaAlAs laser diode with a TQW (triple quantum well) structure. It is suitable as a light source for various types of optical equipment.

Features

- Infrared light output: $\lambda_p = 840$ to 860 nm
- High Power: standard continuous operation at 40mW (CW), pulsed operation at 50mW
- Built-in monitor photodiode
- Single longitudinal mode



Absolute Maximum Ratings

($T_C = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Optical output power	P_O	40	mW
Pulse optical output power	$P_{O(\text{pulse})}$	50 *	mW
LD reverse voltage	$V_{R(\text{LD})}$	2	V
PD reverse voltage	$V_{R(\text{PD})}$	30	V
Operating temperature	T_{opr}	-10 to $+60$	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to $+85$	$^\circ\text{C}$

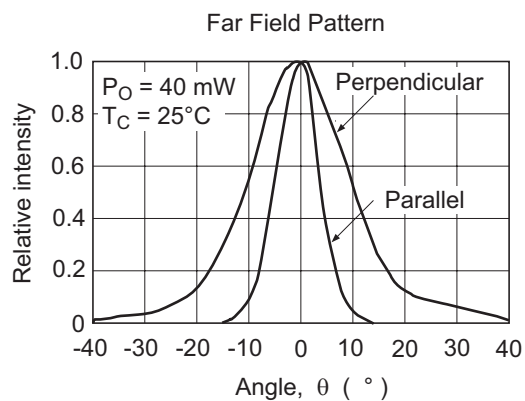
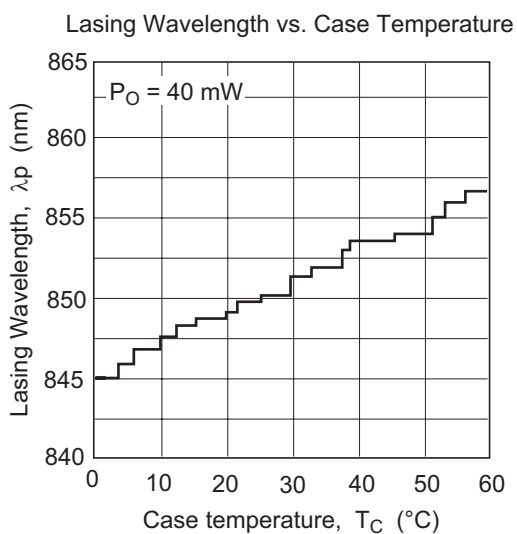
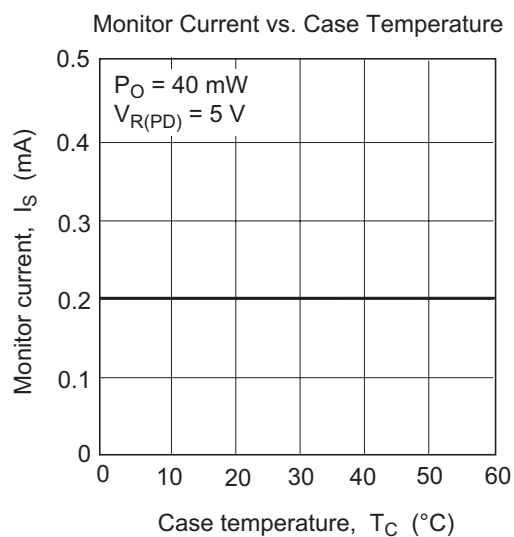
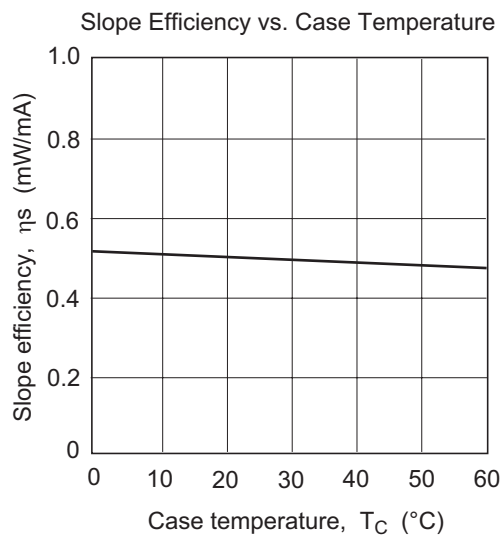
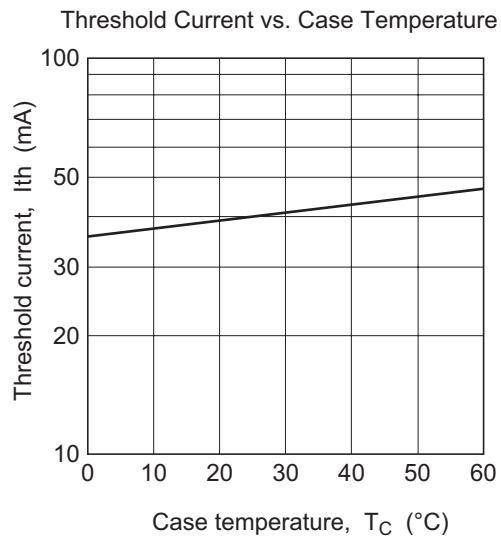
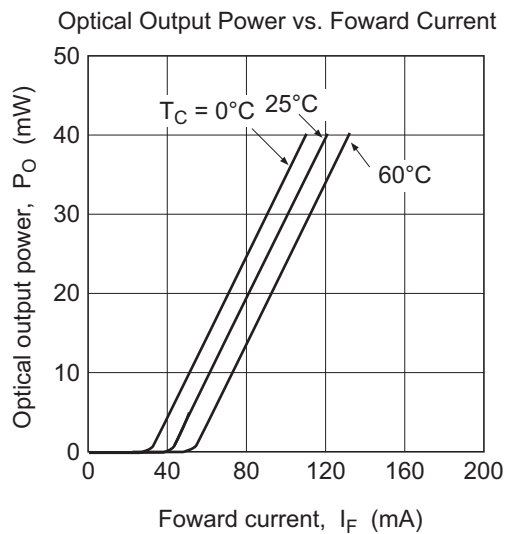
Note: Pulse condition : Pulse width $\leq 1 \mu\text{s}$, duty $\leq 50\%$

Optical and Electrical Characteristics

($T_C = 25^\circ\text{C}$)

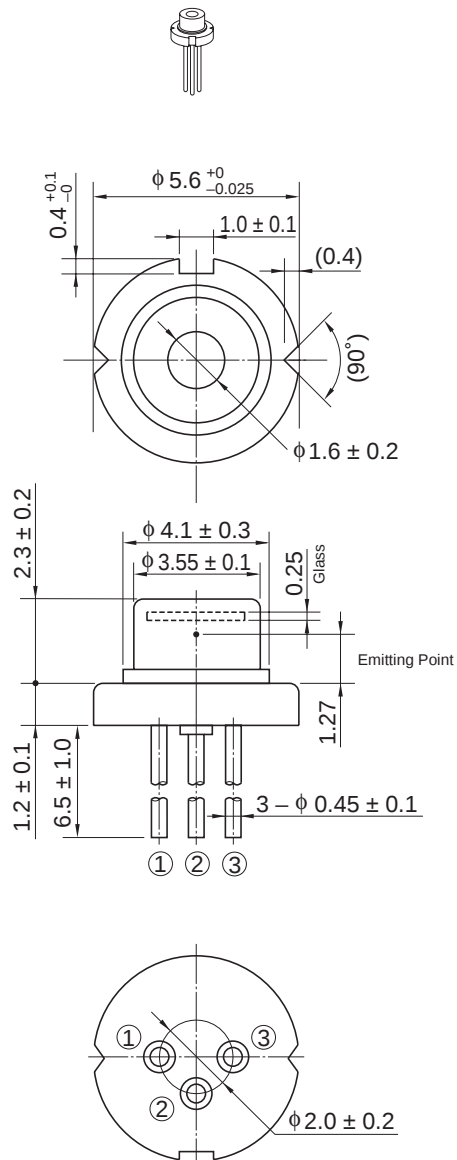
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Threshold current	I_{th}	—	40	70	mA	—
Slope efficiency	η_S	0.4	0.5	0.9	mW/mA	$24(\text{mW}) / (I_{(32\text{mW})} - I_{(8\text{mW})})$
Operating current	I_{OP}	—	120	160	mA	$P_O = 40 \text{ mW}$
Beam divergence parallel to the junction	$\theta_{//}$	7	10	14	$^\circ$	$P_O = 40 \text{ mW}$, FWHM
Beam divergence perpendicular to the junction	$\theta_{\perp}$	18	22	32	$^\circ$	$P_O = 40 \text{ mW}$, FWHM
Lasing wavelength	λ_p	840	850	860	nm	$P_O = 40 \text{ mW}$
Monitor current	I_S	0.08	0.2	0.40	mA	$P_O = 40 \text{ mW}$, $V_{R(\text{PD})} = 5 \text{ V}$

Typical Characteristic Curves



Package Dimensions

As of July, 2002
Unit: mm



OPJ Code	LD/MG
JEDEC	—
JEITA	—
Mass (reference value)	0.3 g

Cautions

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1. The laser light is harmful to human body especially to eye no matter what directly or indirectly. The laser beam shall be observed or adjusted through infrared camera or equivalent.
2. This product contains gallium arsenide (GaAs), which may seriously endanger your health even at very low doses. Please avoid treatment which may create GaAs powder or gas, such as disassembly or performing chemical experiments, when you handle the product.
When disposing of the product, please follow the laws of your country and separate it from other waste such as industrial waste and household garbage.
3. Definition of items shown in this CAS is in accordance with that shown in Opto Device Databook issued by OPJ unless otherwise specified.

Sales Offices



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